MITSUBISHI RF POWER TRANSISTOR

2SC1972

NPN EPITAXIAL PLANAR TYPE

DESCRIPTION

2SC1972 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers on VHF band mobile radio applications.

FEATURES

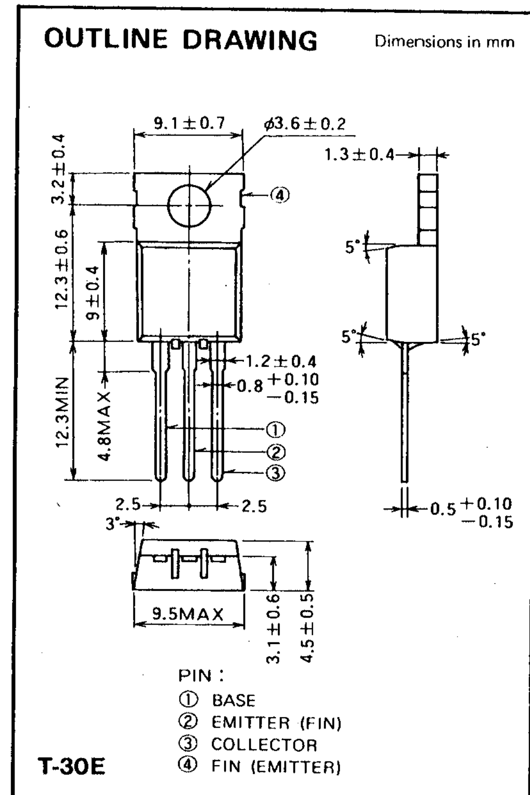
- High power gain: $G_{pe} \geq 7.5dB$
  $@V_{CC} = 13.5V, P_O = 14W, f = 175MHz$
- Emitter ballasted construction, gold metallization for high reliability and good performances.
- TO-220 package similar is combinient for mounting.
- Ability of withstanding more than 20:1 load VSWR when operated at $V_{CC} = 15.2V, P_O = 18W, f = 175MHz$.
- Equivalent input/output series impedance:
  Zin=2.1+j3.1Ω @Po=14W, Vcc=13.5V, f=175MHz
  Zout=5.5+j4.5Ω

APPLICATION

10 to 14 watts output power amplifiers in VHF band mobile radio applications.

OUTLINE DRAWING

Dimensions in mm



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CBO}	Collector to base voltage		35	V
V_{EBO}	Emitter to base voltage		4	V
V_{CEO}	Collector to emitter voltage	$R_{BE}=\infty$	17	V
I_C	Collector current		3.5	A
P_C	Collector dissipation	Ta=25°C	1.5	W
		Tc=25°C	25	W
T_j	Junction temperature		175	°C
T_{stg}	Storage temperature		−55 to 175	°C
Rth-a	Thermal resistance	Junction to ambient	100	°C/W
Rth-c		Junction to case	6	°C/W

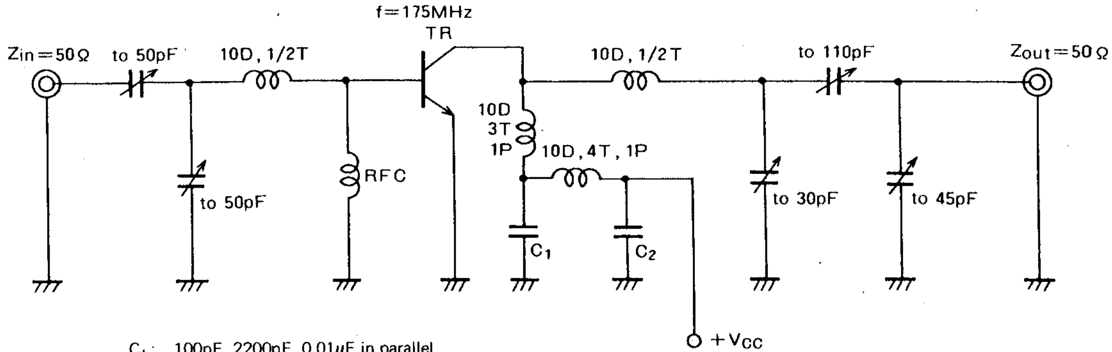
Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	I_E=10mA, I_C=0	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	I_C=10mA, I_E=0	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	I_C=50mA, $R_{BE}=\infty$	17			V
I_{CBO}	Collector cutoff current	V_{CB}=25V, I_E=0			1000	μA
I_{EBO}	Emitter cutoff current	V_{EB}=3V, I_C=0			500	μA
h_{FE}	DC forward current gain*	V_{CE}=10V, I_C=0.1A	10	50	180	—
P_O	Output power	V_{CC}=13.5V, P_{in}=2.5W, f=175MHz	14	15		W
η_C	Collector efficiency		60	70		%

Note. *Pulse test, P_W=150μs, duty=5%.
Above parameters, ratings, limits and conditions are subject to change.

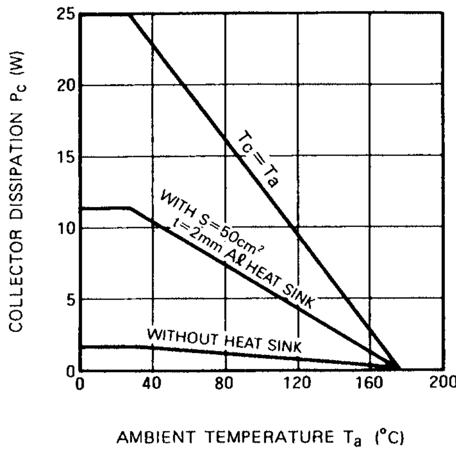
TEST CIRCUIT



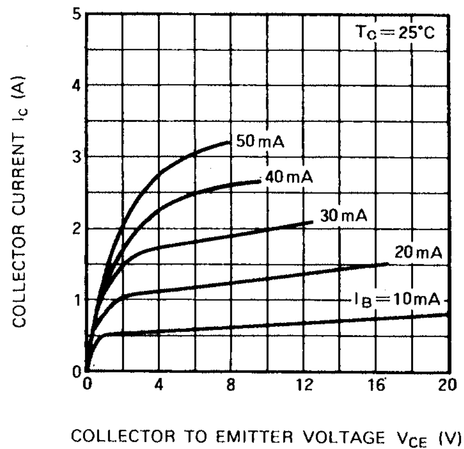
C_1: 100pF, 2200pF, 0.01μF in parallel
C_2: 100pF, 2200pF, 0.01μF, 10μF in parallel
Notes: All coil are made from 1.5mm] silver plated copper wire
D: Inner diameter of coil
T: Turn number of coil
P: Pitch of coil

TYPICAL PERFORMANCE DATA

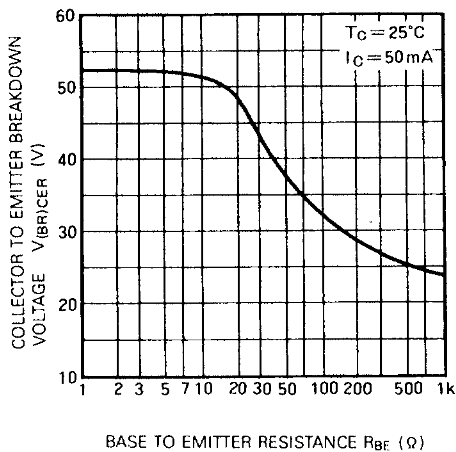
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



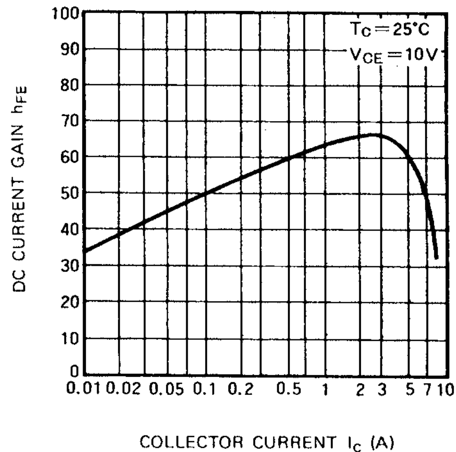
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



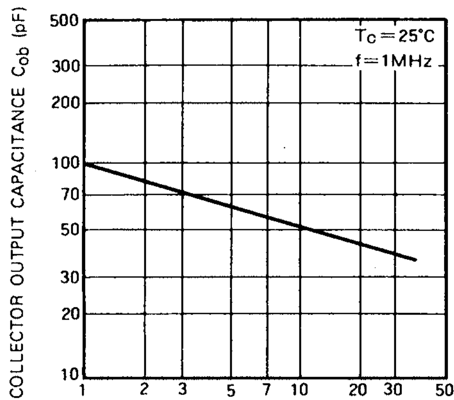
COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE



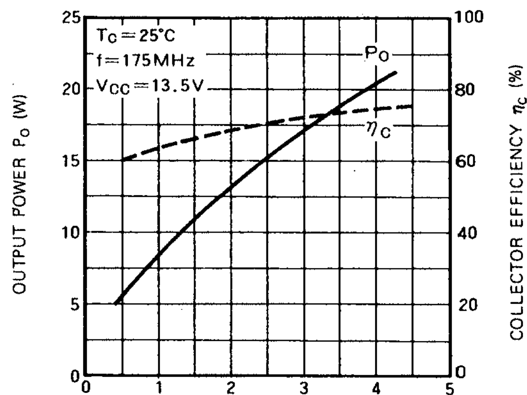
DC CURRENT GAIN VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER



OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE